

# ***PDC4UV7284A-(75/102/103)T-S***

## ***32MByte (4M x 72) CMOS, PC/100***

### ***Synchronous DRAM Module - ECC***

#### **General Description**

The PDC4UV7284A-(75/102/103)T-S is a high performance, 32-megabyte synchronous, dynamic RAM module organized as 4M words by 72 bits, in a 168-pin, JEDEC ECC configuration, dual-in-line memory module (DIMM) package.

The module utilizes eighteen Fujitsu MB81F16822B-(75/102/103) FN CMOS 2Mx8 synchronous dynamic RAMs in surface mount package (TSOP) on an epoxy laminated substrate. Each device is accompanied by a decoupling capacitor for improved noise immunity.

A 256 Byte Serial EEPROM contains the module configuration information.

#### **Features**

- High Density 32MByte
- Cycle Time: 7.5ns (-75), 10ns (-102), 10ns (-103)
- Low Power: Active 6.6W (-75), 5.8W (-102), 5.5W (-103)
- LVTTTL-compatible inputs and outputs
- Separate power and ground planes to improve noise immunity
- Single power supply of 3.3V±0.3V
- Height: 1.250 inch

#### **ABSOLUTE MAXIMUM RATINGS**

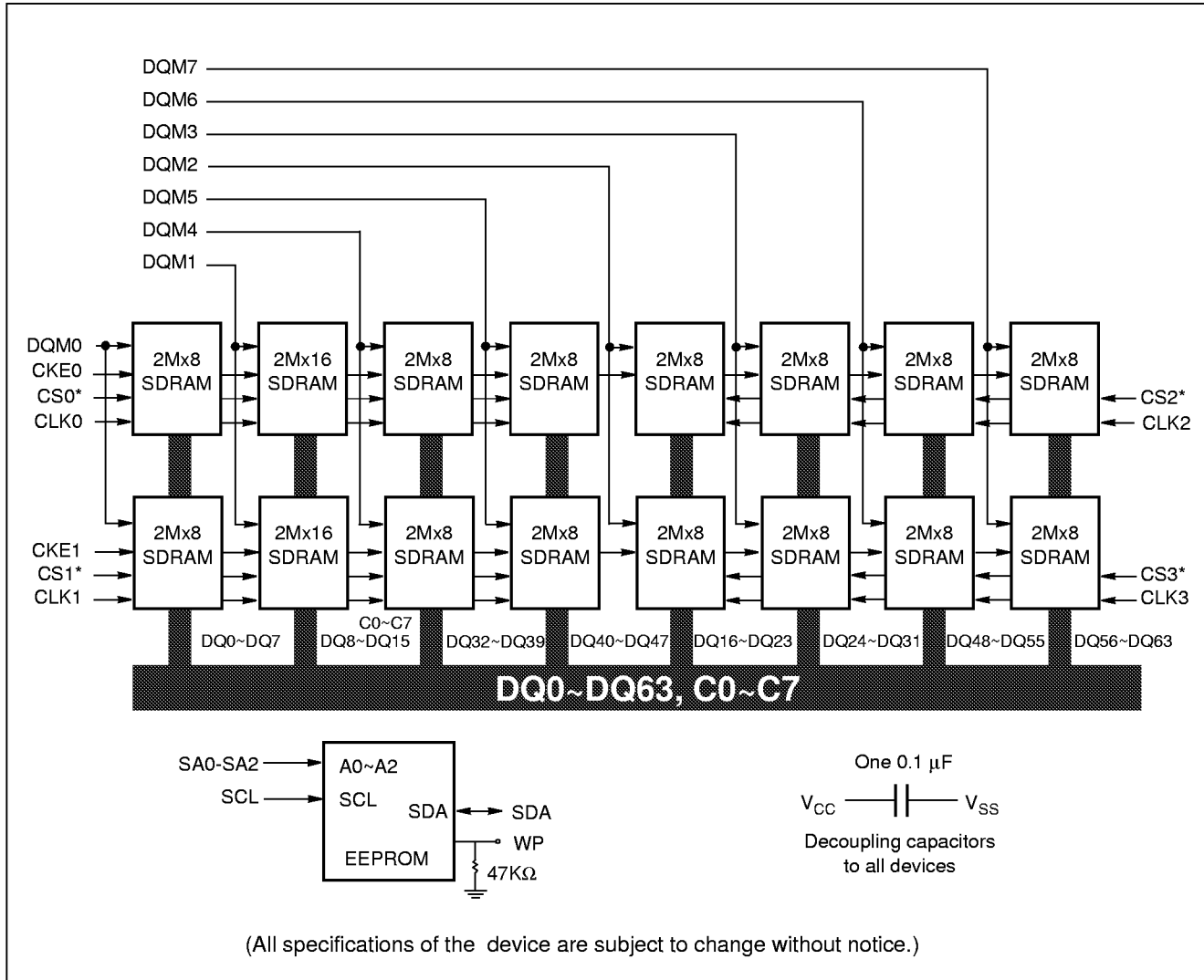
Item	Symbol	Ratings	Unit
Voltage on any pin relative to V <sub>SS</sub>	V <sub>T</sub>	-0.5 to +4.6	V
Power Dissipation	P <sub>T</sub>	23.4	W
Operating Temperature	T <sub>opr</sub>	0 to +70	°C
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C
Short Circuit Output Current	I <sub>OS</sub>	±50	mA

#### **RECOMMENDED DC OPERATING CONDITIONS**

(T<sub>A</sub> = 0 to +70 °C)

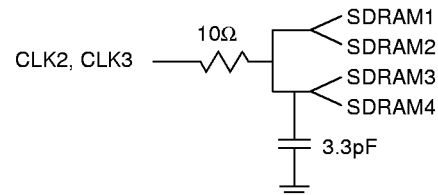
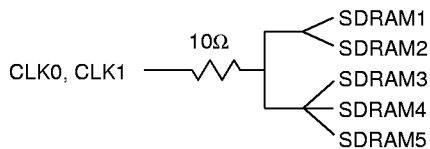
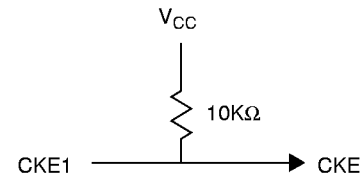
Symbol	Parameter	Min	Typ	Max	Unit
V <sub>CC</sub>	Supply Voltage	3.0	3.3	3.6	V
V <sub>SS</sub>	Ground	0	0	0	V
V <sub>IH</sub>	Input High voltage	2.0	-	V <sub>CC</sub> +0.5	V
V <sub>IL</sub>	Input Low voltage	-0.5	-	0.8	V

### Functional Diagram



- Notes:
1. A0~A10, BA0 to all devices
  2. WE\*, RAS\*, CAS\* to all devices.
  3. Data and CLKs are terminated using 10 ohm series resistors.
  4. CKE1 has a 10K ohm pull-up to Vcc.
  5. Each 2Mx16 block comprises two 2Mx8 SDRAM devices.
  6. DQMs vs Data I/Os
 

DQMB0 controls	DQ0 ~ DQ7
DQMB1 controls	DQ8 ~ DQ15, C0~C7
DQMB2 controls	DQ16 ~ DQ23
DQMB3 controls	DQ24 ~ DQ31
DQMB4 controls	DQ32 ~ DQ39
DQMB5 controls	DQ40 ~ DQ47
DQMB6 controls	DQ48 ~ DQ55
DQMB7 controls	DQ56 ~ DQ63
  7. Clock wiring



## PDC4UV7284A-(75/102/103)T-S

### Pin Name

A0~A10/AP	Addresses	CS0*~CS3*	Chip Select
BA0	Bank Select Address	WE*	Write Enable
DQ0~DQ63, C0~C7	Data Inputs/Outputs	SA0~SA2	Decode Input
CLK0~CLK3	Clock Inputs	SCL	Serial Clock
RAS*	Row Address Strobes	SDA	Serial Data Input/Output
CAS*	Column Address Strobes	WP	Write Protect
CKE0, CKE1	Clock Enables	V <sub>CC</sub>	Power Supply
DQMB0~DQMB7	DQ Mask Enables	V <sub>SS</sub>	Ground
		NC	No Connection

Pin No.	Pin Designation	Pin No.	Pin Designation	Pin No.	Pin Designation	Pin No.	Pin Designation
1	V <sub>SS</sub>	43	V <sub>SS</sub>	85	V <sub>SS</sub>	127	V <sub>SS</sub>
2	DQ0	44	NC	86	DQ32	128	CKE0
3	DQ1	45	CS2*	87	DQ33	129	CS3
4	DQ2	46	DQMB2	88	DQ34	130	DQMB6
5	DQ3	47	DQMB3	89	DQ35	131	DQMB7
6	V <sub>CC</sub>	48	NC	90	V <sub>CC</sub>	132	NC
7	DQ4	49	V <sub>CC</sub>	91	DQ36	133	V <sub>CC</sub>
8	DQ5	50	NC	92	DQ37	134	NC
9	DQ6	51	NC	93	DQ38	135	NC
10	DQ7	52	C2	94	DQ39	136	C6
11	DQ8	53	C3	95	DQ40	137	C7
12	V <sub>SS</sub>	54	V <sub>SS</sub>	96	V <sub>SS</sub>	138	V <sub>SS</sub>
13	DQ9	55	DQ16	97	DQ41	139	DQ48
14	DQ10	56	DQ17	98	DQ42	140	DQ49
15	DQ11	57	DQ18	99	DQ43	141	DQ50
16	DQ12	58	DQ19	100	DQ44	142	DQ51
17	DQ13	59	V <sub>CC</sub>	101	DQ45	143	V <sub>CC</sub>
18	V <sub>CC</sub>	60	DQ20	102	V <sub>CC</sub>	144	DQ52
19	DQ14	61	NC	103	DQ46	145	NC
20	DQ15	62	NC	104	DQ47	146	NC
21	C0	63	CKE1	105	C4	147	NC
22	C1	64	V <sub>SS</sub>	106	C5	148	V <sub>SS</sub>
23	V <sub>SS</sub>	65	DQ21	107	V <sub>SS</sub>	149	DQ53
24	NC	66	DQ22	108	NC	150	DQ54
25	NC	67	DQ23	109	NC	151	DQ55
26	V <sub>CC</sub>	68	V <sub>SS</sub>	110	V <sub>CC</sub>	152	V <sub>SS</sub>
27	WE*	69	DQ24	111	CAS*	153	DQ56
28	DQMB0	70	DQ25	112	DQMB4	154	DQ57
29	DQMB1	71	DQ26	113	DQMB5	155	DQ58
30	CS0*	72	DQ27	114	CS1*	156	DQ59
31	NC	73	V <sub>CC</sub>	115	RAS*	157	V <sub>CC</sub>
32	V <sub>SS</sub>	74	DQ28	116	V <sub>SS</sub>	158	DQ60
33	A0	75	DQ29	117	A1	159	DQ61
34	A2	76	DQ30	118	A3	160	DQ62
35	A4	77	DQ31	119	A5	161	DQ63
36	A6	78	V <sub>SS</sub>	120	A7	162	V <sub>SS</sub>
37	A8	79	CLK2	121	A9	163	CLK3
38	A10/AP (Note)	80	NC	122	BA0 (Note)	164	NC
39	NC	81	WP	123	NC	165	SA0
40	V <sub>CC</sub>	82	SDA	124	V <sub>CC</sub>	166	SA1
41	V <sub>CC</sub>	83	SCL	125	CLK1	167	SA2
42	CLK0	84	V <sub>CC</sub>	126	NC	168	V <sub>CC</sub>

- Notes: 1. Address A10/AP : Initiates Auto-Precharge  
2. Address BA0 : Bank select within the SDRAM devices.

**SERIAL PD INFORMATION**

Byte#	Function Described	Function Supported			Hex Value		
		75	102	103	75	102	103
0	# Bytes Written into serial memory at module mfr	128 bytes			80h		
1	Total # bytes of SPD memory device	256 bytes			08h		
2	Fundamental memory type	SDRAM			04h		
3	# Row Address on this assembly	11			0Bh		
4	# Column Addresses on this assembly	9			09h		
5	# Module Banks on this assembly	2			02h		
6	Data Width of this assembly	72 bits			48h		
7	Data Width of this assembly (continued)				00h		
8	Voltage interface standard of this assembly	LVTTL			01h		
9	SDRAM cycle time at CL=3 (tCLK)	7.5ns	10ns	10ns	75h	A0h	A0h
10	SDRAM Access from Clock at CL=3 (tAC)	6ns	6ns	6ns	60h	60h	60h
11	DIMM configuration type	ECC			02h		
12	Refresh Rate/Type	S/R, Normal 15.6 ms			80h		
13	SDRAM Width Primary DRAM	x8			08h		
14	ECC SDRAM Data Width	x8			08h		
15	Min. clock delay, Back to Back Random Column Addresses (ICCD)	1CLK			01h		
16	Burst Length Supported	1, 2, 4, 8 & Full			8Fh		
17	# Banks on each SDRAM device	2			02h		
18	CAS# Latency	2, 3			06h		
19	CS# Latency	0			01h		
20	Write Latency	0			01h		
21	SDRAM Module Attribute	Non-Buffered/Registered			00h		
22	SDRAM Device Attribute	Vcc, B/R, S/W, P/A, A/P			0Eh		
23	Min Clock cycle Time at CL=2 (tCLK)	11.5ns	10ns	12ns	B5h	A0h	C0h
24	Max. Data Access Time from clock at CL=2 (tAC)	7ns	6ns	8ns	70h	60h	80h
25	Min Clock cycle Time at CL=1 (tCLK)	N/A			FFh		
26	Max. Data Access Time from clock at CL=1 (tAC)	N/A			FFh		
27	Min. Row Precharge Time (tRP)	22.5ns	20ns	20ns	17h	14h	14h
28	Min. Row Active Delay (tRRD)	15ns	20ns	20ns	0Fh	14h	14h
29	Min. RAS to CAS Delay (tRCD)	22.5ns	20ns	20ns	17h	14h	14h
30	Min. RAS Pulse Width (tRAS)	45ns	50ns	50ns	2Dh	32h	32h
31	Module Bank Density	16MB			04h		
32	Address and Command Signal Input Setup Time before clock (t <sub>SI</sub> )	2ns	2ns	2ns	20h	20h	20h
33	Address and Command Signal Input Hold Time after clock (t <sub>HI</sub> )	1ns	1ns	1ns	10h	10h	10h
34	Data Signal Input Setup Time before clock (t <sub>SI</sub> )	2ns	2ns	2ns	20h	20h	20h
35	Data Signal Input Hold Time after clock (t <sub>HI</sub> )	1ns	1ns	1ns	10h	10h	10h
36-61	Superset Information				FFh		
62	SPD Revision	Rev. 2			02h		
63	Checksum for bytes 0-62	JEDEC Calculation			JEDEC Calculation		

## PDC4UV7284A-(75/102/103)T-S

### SERIAL PD INFORMATION (CONTINUED)

Byte#	Function Described	Function Supported			Hex Value		
		75	102	103	75	102	103
64	Manufacturers JEDEC ID code per JEP-106E	Continuation code			7Fh		
65	Manufacturers JEDEC ID code per JEP-106E	SMART's ID			94h		
66-71	Manufacturers JEDEC ID code per JEP-106E	None			FFh		
72	Manufacturing location	Mfr Specific Data					
73	Manufacturer's Part Number	P			50h		
74	Manufacturer's Part Number	D			44h		
75	Manufacturer's Part Number	C			43h		
76	Manufacturer's Part Number	4			34h		
77	Manufacturer's Part Number	U			55h		
78	Manufacturer's Part Number	V			56h		
79	Manufacturer's Part Number	7			37h		
80	Manufacturer's Part Number	2			32h		
81	Manufacturer's Part Number	8			38h		
82	Manufacturer's Part Number	4			34h		
83	Manufacturer's Part Number	A			41h		
84	Manufacturer's Part Number	7	1	1	37h	31h	31h
85	Manufacturer's Part Number	5	0	0	35h	30h	30h
86	Manufacturer's Part Number	T	2	3	54h	32h	33h
87	Manufacturer's Part Number	S	T	T	53h	54h	54h
88	Manufacturer's Part Number	None	S	S	FFh	53h	53h
89	Manufacturer's Part Number	None			FFh		
90	Manufacturer's Part Number	None			FFh		
91	Revision Code	Mfr Specific Data			Mfr Specific Data		
92	Revision Code	None			FFh		
93	Manufacturing Date	DATE			DATE		
94	Manufacturing Date	DATE			DATE		
95-98	Assembly Serial Number	Serial Number			S.No.		
99	Manufacturer Specific Data	S			53h		
100	Manufacturer Specific Data	M			4Dh		
101	Manufacturer Specific Data	A			41h		
102	Manufacturer Specific Data	R			52h		
103	Manufacturer Specific Data	T			54h		
104	Manufacturer Specific Data	M			4Dh		
105	Manufacturer Specific Data	o			6Fh		
106	Manufacturer Specific Data	d			64h		
107	Manufacturer Specific Data	u			75h		
108	Manufacturer Specific Data	l			6Ch		
109	Manufacturer Specific Data	a			61h		
110	Manufacturer Specific Data	r			72h		
111	Manufacturer Specific Data	T			54h		
112	Manufacturer Specific Data	e			65h		
113	Manufacturer Specific Data	c			63h		
114	Manufacturer Specific Data	h			68h		
115	Manufacturer Specific Data	n			6Eh		
116	Manufacturer Specific Data	o			6Fh		
117	Manufacturer Specific Data	l			6Ch		
118	Manufacturer Specific Data	o			6Fh		
119	Manufacturer Specific Data	g			67h		
120	Manufacturer Specific Data	i			69h		
121	Manufacturer Specific Data	e			65h		
122	Manufacturer Specific Data	s			73h		
123	Manufacturer Specific Data	None			FFh		
124	Manufacturer Specific Data	None			FFh		
125	Manufacturer Specific Data	None			FFh		
126	Manufacturer Specific Data	None			FFh		
127	Manufacturer Specific Data	None			FFh		
128-255	Open for CPQ Use for Read & Write	None			FFh		

**DC CHARACTERISTICS**
**(AT RECOMMENDED OPERATING CONDITIONS UNLESS OTHERWISE NOTED) NOTES 1,2**

Parameter		Symbol	Conditions	Value		Unit	
				Min.	Max.		
Output High Voltage		$V_{OH(DC)}$	$I_{OH} = -2mA$	2.4	-	V	
Output Low Voltage		$V_{OL(DC)}$	$I_{OL} = 2mA$	-	0.4	V	
Input Leakage Current (Any Input)		$I_{LI}$	$0V \leq V_{IN} \leq V_{CC}$ ; All other pins not under test = 0V	-90	90	$\mu A$	
Output Leakage Current		$I_{LO}$	$0V \leq V_{IN} \leq V_{CC}$ $D_{out} = \text{Disable}$	-10	10	$\mu A$	
Operating Current (Average Power Supply Current)		$I_{CC1S}$	Burst: Length=4, $t_{RC} = \text{min}$ for BL=4, $t_{CK} = \text{min}$ . One bank- active, Outputs open, Addresses changed up to 3-times during $t_{RC}$ (min), $0V \leq V_{in} \leq V_{CC}$		1386	mA	
				75	-		1260
				102	-		1170
		$I_{CC1D}$	Burst: Length=4 (each bank), $t_{RC} = \text{min}$ for BL=4 (each bank), $t_{CK} = \text{min}$ . All banks active, Output open, Addresses changed up to 3-times during $t_{RC}$ (min), $0V \leq V_{in} \leq V_{CC}$	75	-	1836	mA
				102	-	1620	
				103	-	1530	
Precharge Standby Current (Power Supply Current)		$I_{CC2P}$	CKE= $V_{IL}$ , All banks idle, $t_{CK} = \text{min}$ , Power down mode, $0V \leq V_{in} \leq V_{CC}$	-	7.2	mA	
		$I_{CC2PS}$	CKE= $V_{IL}$ , All banks idle, CLK=H or L, Power down mode, $0V \leq V_{in} \leq V_{CC}$	-	7.2		
Precharge Standby Current (Power Supply Current)		$I_{CC2N}$	CKE= $V_{IH}$ , All banks idle, $t_{CK} = \text{min}$ , NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, $0V \leq V_{in} \leq V_{CC}$	75	-	486	mA
				102	-	360	
				103	-	360	
Precharge Standby Current (Power Supply Current)		$I_{CC2NS}$	CKE= $V_{IH}$ , All banks idle, CLK=H or L, Input signals are stable, $0V \leq V_{in} \leq V_{CC}$	-	270		

## PDC4UV7284A-(75/102/103)T-S

(Continued)

Parameter	Symbol	Test Condition	Value		Unit
			Min.	Max.	
Active Standby Current (Power Supply Current)	$I_{CC3P}$	CKE= $V_{IL}$ , Any bank active, $t_{CK}=\text{min}$ , $0V \leq V_{in} \leq V_{CC}$	-	90	mA
	$I_{CC3PS}$	CKE= $V_{IL}$ , Any bank active, CLK = H or L, $0V \leq V_{in} \leq V_{CC}$	-	54	mA
Active Standby Current (Power Supply Current)	75	$I_{CC3N}$ CKE= $V_{IH}$ , Any bank active, $t_{CK}=\text{min}$ , NOP commands only, Input signals (except to CMD) are changed one time during 3 clock cycles, $0V \leq V_{in} \leq V_{CC}$	-	972	mA
	102		-	720	mA
	103		-	720	mA
Active Standby Current (Power Supply Current)	$I_{CC3NS}$	CKE= $V_{IH}$ , Any bank active, CLK = H or L, $0V \leq V_{in} \leq V_{CC}$	-	450	mA
Burst mode Current (Average Power supply current)	75	$I_{CC4}$ $t_{CK}=\text{min}$ , Burst length=4, Outputs open, Multiple-banks active, Gapless data, $0V \leq V_{in} \leq V_{CC}$	-	1836	mA
	102		-	1440	
	103		-	1440	
Refresh Current #1 (Average Power Supply Current)	75	$I_{CC5}$ Auto-refresh; $t_{CK}=\text{min}$ , $t_{RC}=\text{min}$ , $0V \leq V_{in} \leq V_{CC}$	-	1386	mA
	102		-	1080	
	103		-	1080	
Refresh Current #2 (Average Power Supply Current)	$I_{CC6}$	Self-refresh; $t_{CK}=\text{min}$ , CKE $\leq 0.2V$ , $0V \leq V_{in} \leq V_{CC}$	-	7.2	mA
Refresh Current #2 (Average Power Supply Current)	$I_{CC6A}$	Asynchronous Self-refresh (by CLK stop); CKE $\leq 0.2V$ , CLK = $V_{IL}$ , $0V \leq V_{in} \leq V_{CC}$	-	7.2	mA

†CL = CAS\* Latency

- Notes:
- $I_{CC}$  depends on the output termination or load conditions, clock cycle rate, and signal clocking rate;  
The specified values are obtained with the output open and no termination register.
  - An initial pause (DESL or NOP) of 200  $\mu\text{s}$  is required after power-up followed by a minimum of eight Auto-refresh cycles.

**CAPACITANCE**

(TA = +25°C, VCC = 3.3V±0.3V)

Parameter	Symbol	Max.	Unit	Note
Input Capacitance (Address, WE*, RAS*, CAS*)	C <sub>I1</sub>	95	pF	1
Input Capacitance (DQMB0, DQMB2~DQMB7)	C <sub>I2</sub>	15	pF	1
Input Capacitance (DQMB1)	C <sub>I3</sub>	25	pF	1
Input Capacitance (CS0*, CS1*, CE0, CE1)	C <sub>I4</sub>	30	pF	1
Input Capacitance (CS2*, CS3*, CLK0~CLK3)	C <sub>I5</sub>	25	pF	1
Input/Output Capacitance (DQ0~DQ63, C0~C7)	C <sub>I/O</sub>	19	pF	1, 2

- Notes: 1. Capacitance is measured with Boonton Meter or effective capacitance method.  
 2. CAS\* - V<sub>IH</sub> to disable D<sub>out</sub>.

**AC CHARACTERISTICS: MB81F16822B-(75/102/103)**

(At recommended operating conditions unless otherwise noted) Notes 2,3,4

Parameter		Symbol	Unit	-75		-102		-103		Notes
				Min.	Max.	Min.	Max.	Min.	Max.	
Clock Period	CAS Latency=2	t <sub>CK2</sub>	ns	11.5	-	10	-	12	-	
	CAS Latency=3	t <sub>CK3</sub>		7.5	-	10	-	10	-	
Clock High Time		t <sub>CH</sub>	ns	2.5	-	3	-	3	-	
Clock Low Time		t <sub>CL</sub>	ns	2.5	-	3	-	3	-	
Input Setup Time		t <sub>SI</sub>	ns	2	-	2	-	2	-	
Input Hold Time		t <sub>HI</sub>	ns	1	-	1	-	1	-	
Access time from Clock (t <sub>CK</sub> =min)	CAS Latency=2	t <sub>AC2</sub>	ns	-	7	-	6	-	8	5,6
	CAS Latency=3	t <sub>AC3</sub>		-	6	-	6	-	6	
Output In Low-Z		t <sub>LZ</sub>	ns	0	-	0	-	0	-	
Output in High-Z	CAS Latency=2	t <sub>HZ2</sub>	ns	3	7	3	6	3	8	7
	CAS Latency=3	t <sub>HZ3</sub>		2	6	3	6	3	6	
Output Hold Time	CAS Latency=2	t <sub>OH</sub>	ns	3	-	3	-	3	-	
	CAS Latency=3			2	-	3	-	3	-	
Time between Auto-Refresh command Interval		t <sub>REFI</sub>	μs	-	15.6	-	15.6	-	15.6	
CKE Low (or CLK Low) Hold Time for Asynchronous Self-Refresh Entry		t <sub>ASE</sub>	μs	100	200	100	200	100	200	
Transition Time		t <sub>T</sub>	ns	0.5	2	0.5	2	0.5	2	
CKE Set Up time for Power Down Exit		t <sub>CKSP</sub>	ns	3	-	3	-	3	-	



## PDC4UV7284A-(75/102/103)T-S

### BASE VALUES FOR CLOCK COUNT/LATENCY: MB81F16822B-(75/102/103)

Parameter	Symbol	Unit	-75		-102		-103		Notes
			Min.	Max.	Min.	Max.	Min.	Max.	
$\overline{\text{RAS}}$ Cycle Time	$t_{\text{RC}}$	ns	67.5	-	70	-	70	-	8
$\overline{\text{RAS}}$ Precharge Time	$t_{\text{RP}}$	ns	22.5	-	20	-	20	-	
$\overline{\text{RAS}}$ Active Time	$t_{\text{RAS}}$	ns	45	110000	50	110000	50	110000	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	$t_{\text{RCD}}$	ns	22.5	-	20	-	20	-	9
Write Recovery Time	$t_{\text{WR}}$	ns	7.5	-	10	-	10	-	
Data-in to Precharge Lead Time	$t_{\text{DPL}}$	ns	7.5	-	10	-	10	-	
Data-in to Active/ Refresh command period	CAS Latency=2 $t_{\text{DAL2}}$	ns	$1\text{cyc}+t_{\text{RP}}$	-	$1\text{cyc}+t_{\text{RP}}$	-	$1\text{cyc}+t_{\text{RP}}$	-	
	CAS Latency=3 $t_{\text{DAL3}}$		$2\text{cyc}+t_{\text{RP}}$	-	$2\text{cyc}+t_{\text{RP}}$	-	$2\text{cyc}+t_{\text{RP}}$	-	
Mode Register set cycle Time	$t_{\text{RSC}}$	ns	15	-	20	-	20	-	
$\overline{\text{RAS}}$ to $\overline{\text{RAS}}$ Bank Active Delay Time	$t_{\text{RRD}}$	ns	15	-	20	-	20	-	

### CLOCK COUNT FORMULA

(Note 10)

$$\text{Clock} \geq \frac{\text{Base Value}}{\text{Clock Period}} \quad (\text{Round off a whole number})$$

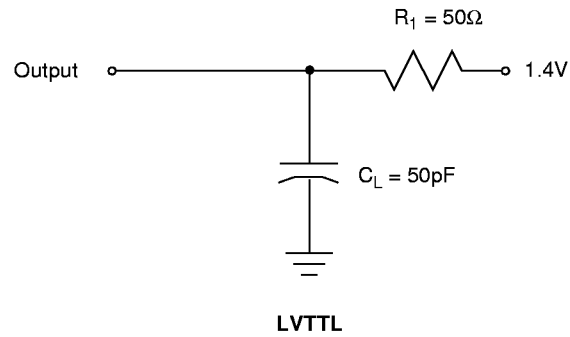
### LATENCY-FIXED VALUES: MB81F16822B-(75/102/103)

(The latency values on these parameters are fixed regardless of clock period)

Parameter	Symbol	Unit	-75	-102	-103	Notes
CKE to Clock Disable	$I_{\text{CKE}}$	cycle	1	1	1	
DQM to Output in High-Z	$I_{\text{DQZ}}$	cycle	2	2	2	
DQM to Input Data Delay	$I_{\text{DQD}}$	cycle	0	0	0	
Last Output to Write Command Delay	$I_{\text{OWD}}$	cycle	2	2	2	
Write Command to Input Data Delay	$I_{\text{DWD}}$	cycle	0	0	0	
Precharge to Output in High-Z Delay	CL = 2 $I_{\text{ROH2}}$	cycle	2	2	2	
	CL = 3 $I_{\text{ROH3}}$		3	3	3	
Burst Stop Command to Output in High-Z Delay	CL = 2 $I_{\text{BSH2}}$	cycle	2	2	2	
	CL = 3 $I_{\text{BSH3}}$		3	3	3	
$\overline{\text{CAS}}$ to $\overline{\text{CAS}}$ Delay (min)	$I_{\text{CCD}}$	cycle	1	1	1	
$\overline{\text{CAS}}$ Bank Delay (min)	$I_{\text{CBD}}$	cycle	1	1	1	

- Notes:
- $I_{\text{CC}}$  depends on the output termination or load conditions, clock cycle rate, and signal clocking rate; The specified values are obtained with the output open and no termination register.
  - An initial pause (DESL or NOP) of 200  $\mu\text{s}$  is required after power-up followed by a minimum of eight Auto-refresh cycles.
  - AC characteristics assume  $t_{\text{T}} = 1 \text{ ns}$  and 50 pF of capacitive load.
  - 1.4 V is the reference level for measuring timing of input signals. Transition times are measured between  $V_{\text{IH}}$  (min) and  $V_{\text{IL}}$  (max).
  - Assumes  $t_{\text{RCD}}$  is satisfied.
  - $t_{\text{AC}}$  also specifies the access time at burst mode.
  - Specified where output buffer is no longer driven.
  - Actual clock count of  $t_{\text{RC}}$  ( $I_{\text{RC}}$ ) will be sum of clock count of  $t_{\text{RAS}}$  ( $I_{\text{RAS}}$ ) and  $t_{\text{RP}}$  ( $I_{\text{RP}}$ ).
  - Operation within the  $t_{\text{RCD}}$  (min) ensures that access time is determined by  $t_{\text{RCD}}$  (min) +  $t_{\text{AC}}$  (max); If  $t_{\text{RCD}}$  is greater than the specified  $t_{\text{RCD}}$  (min), access time is determined by  $t_{\text{AC}}$ .
  - All base values are measured from the clock edge at the command input to the clock edge for the next command input. All clock counts are calculated by a simple formula: clock count equals base value divided by clock period (round off a whole number).

**Fig. 4 - EXAMPLE OF AC TEST LOAD CIRCUIT**

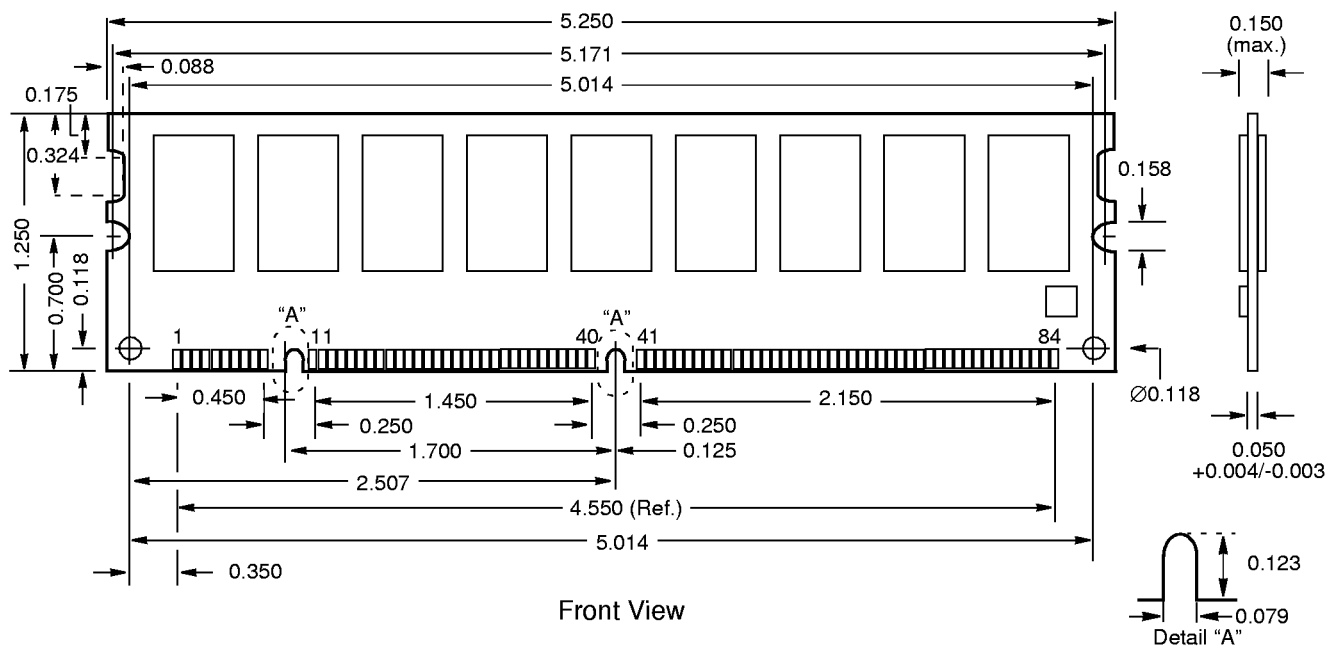


**Note:** AC characteristics are measured in this condition. This load circuits are not applicable for  $V_{OH}$  and  $V_{OL}$ .

# PDC4UV7284A-(75/102/103)T-S

## Physical Dimensions

168-pin (84x2) DIMM



- Notes:
1. All dimensions are in inches.
  2. Pin 85 is behind pin 1 on the back side.

## Ordering Information

P D C 4 U V 72 8 4 A - 102 T - S  
 (1) (2) (3) (4) (5) (6) (7) (8) (9) (10) (11) (12) (13)

- |  |  |
|--|--|
| <p>(1) <b>Memory Type</b><br/>                 S : SDRAM (PC/66)<br/>                 G : SGRAM<br/>                 P : SDRAM-Fast (PC/100)</p> <p>(2) <b>Module Shape</b><br/>                 S : SIMM<br/>                 D : DIMM<br/>                 O : Small Outline DIMM</p> <p>(3) <b>Module Pin Count</b><br/>                 A : 72-pin<br/>                 B : 144-pin<br/>                 C : 168-pin<br/>                 D : 200-pin</p> <p>(4) <b>Word Depth</b><br/>                 1 : 1M<br/>                 2 : 2M<br/>                 4 : 4M<br/>                 8 : 8M<br/>                 16 : 16M<br/>                 256 : 256K<br/>                 512 : 512K</p> <p>(5) <b>Buffer Type</b><br/>                 B : Buffered<br/>                 U : Unbuffered<br/>                 R : Registered</p> <p>(6) <b>Operating Voltage &amp; Power Consumption</b><br/>                 V : 3.3V &amp; LVTTTL &amp; Standard Power<br/>                 L : 3.3V &amp; LVTTTL &amp; Low Power<br/>                 S : 3.3V &amp; SSTL &amp; Standard Power</p> <p>(7) <b>Data Width</b><br/>                 (ex. 64=x64, 72=x72 etc.)</p> <p>(8) <b>Device Configuration</b><br/>                 4 : x4<br/>                 8 : x8<br/>                 1 : x16<br/>                 3 : x32</p> <p>(9) <b>Refresh</b><br/>                 2 : 2krf<br/>                 4 : 4krf<br/>                 8 : 8krf</p> | <p>(10) <b>Module Revision / Applied "Standard" *1</b><br/>                 Blank : Rev. 0<br/>                 A : Rev. 1<br/>                 B : Rev. 2 (etc.)</p> <p>*1 When DRAM device or PCB is revised, the revision is changed</p> <p>(11) <b>Clock Frequency</b><br/>                 SDRAM (PC/66)<br/>                 100 : 100Mhz</p> <p>SDRAM-Fast (PC/100)<br/>                 75 : 133 Mhz (CL=3; t<sub>RCD</sub>=3; t<sub>RP</sub>=3)<br/>                 102 : 100 Mhz (CL=2; t<sub>RCD</sub>=2; t<sub>RP</sub>=2)<br/>                 103 : 100 Mhz (CL=3; t<sub>RCD</sub>=2; t<sub>RP</sub>=2)<br/>                 10 : 100 Mhz (CL=3; t<sub>RCD</sub>=3; t<sub>RP</sub>=3)</p> <p>(12) <b>Package of Component</b><br/>                 T : TSOP</p> <p>(13) <b>Assembly &amp; Test Site</b><br/>                 S : Smart Modular Technologies</p> |
|--|--|

## **PDC4UV7284A-(75/102/103)T-S**

---

### **FUJITSU LIMITED**

For further information please contact:

#### **Japan**

FUJITSU LIMITED  
Memory Marketing Dept.  
4-1-1, Kamikodanaka Nakahara-ku,  
Kawasaki 211-88, Japan  
Tel: +81-44-754-3767  
Fax: +81-44-754-3343  
Internet: <http://www.fujitsu.co.jp/>

#### **North and South America**

FUJITSU MICROELECTRONICS, INC.  
3545 North First Street  
San Jose, CA 95134-1804, USA.  
Tel: +1-408-922-9000  
Fax: +1-408-922-9179  
Customer Response Center (Mon-Fri: 7am-5pm (PST))  
Tel: +1-800-866-8608  
Fax: +1-408-922-9179  
Internet: <http://www.fujitsumicro.com/>

#### **Europe**

FUJITSU MIKROELEKTRONIK GmbH  
Am Siebenstein 6-10  
63303 Dreieich-Buchsschlag  
Germany  
Tel: +49-6103-690-0  
Fax: +49-6103-690-122  
Internet: <http://www.fujitsu-edo.com/>

#### **Asia**

FUJITSU MICROELECTRONICS ASIA PTE LIMITED  
#05-08, 151 Lorong Chuan  
NewTechPark  
Singapore 556741  
Tel: +65-281-0770  
Fax: +65-281-0220  
Internet: <http://www.fsl.com.sg/>

All Rights Reserved.

Circuit diagrams utilizing Fujitsu products are included as a means of illustrating typical semiconductor applications. Complete information sufficient for construction purposes is not necessarily given.

The information given in this document have been carefully checked and is believed to be reliable. However, Fujitsu assumes no responsibility for inaccuracies.

The information contained in this document does not convey any licence under the copyrights, patent rights or trademarks claimed and owned by Fujitsu.

Fujitsu reserves the right to change products or specifications without notice.

No part of this publication may be copied or reproduced in any form or by any means, or transferred to any third party without prior written consent of Fujitsu.

The information contained in this document are not intended for use with equipments which require extremely high reliability such as aerospace equipments, undersea repeaters, nuclear control systems or medical equipments for life support.